

# 2SB1209

## Silicon PNP triple diffusion planar type

For low-frequency amplification

### ■ Features

- High collector-base voltage (Emitter open)  $V_{CBO}$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

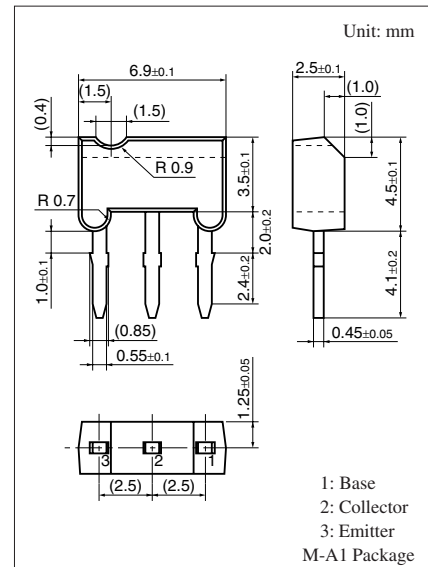
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	-400	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-400	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Peak collector current	$I_{CP}$	-200	mA
Collector power dissipation *	$P_C$	1	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

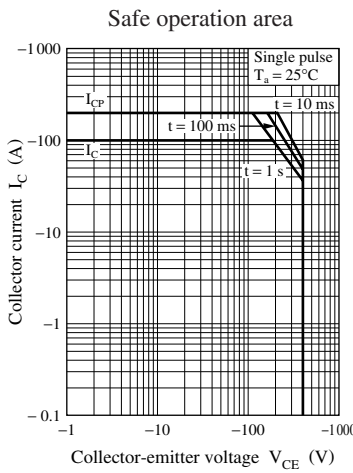
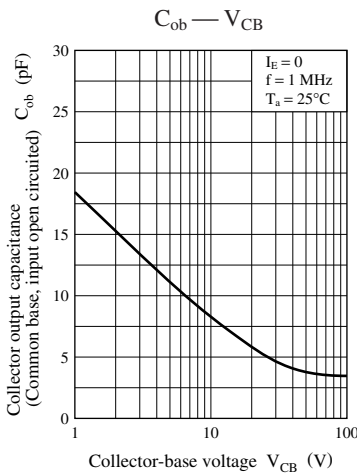
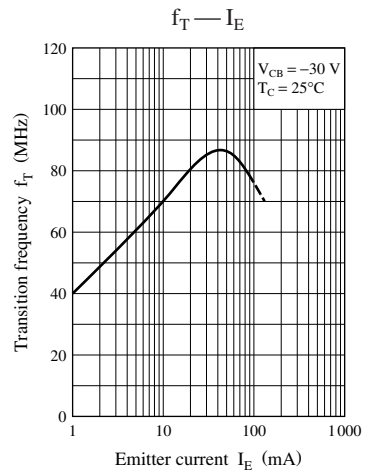
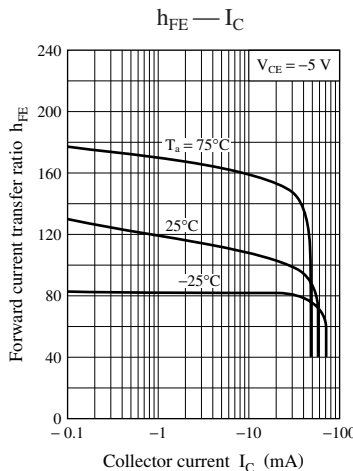
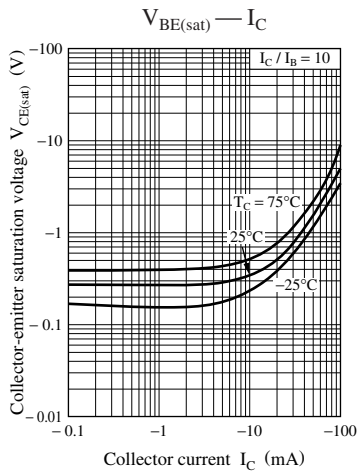
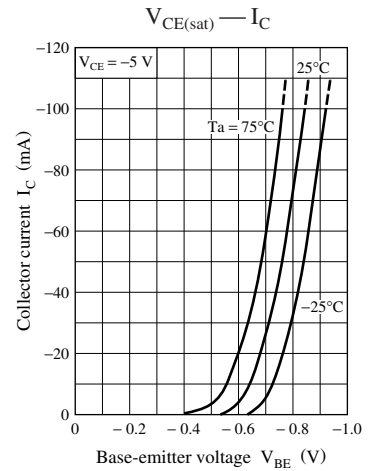
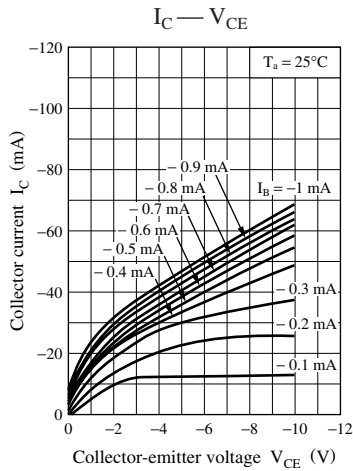
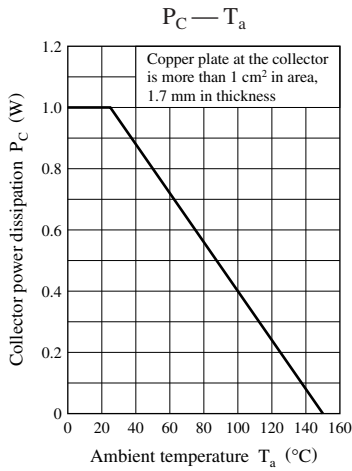
Note) \*: Print circuit board: Copper foil area of  $1\text{ cm}^2$  or more, and the board thickness of 1.7 mm for the collector portion

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -100\ \mu\text{A}$ , $I_E = 0$	-400			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -500\ \mu\text{A}$ , $I_B = 0$	-400			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -100\ \mu\text{A}$ , $I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -5\ \text{V}$ , $I_C = -30\ \text{mA}$	40			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\ \text{mA}$ , $I_B = -1\ \text{mA}$			-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\ \text{mA}$ , $I_B = -5\ \text{mA}$			-1.5	V
Transition frequency	$f_T$	$V_{CB} = -30\ \text{V}$ , $I_E = 20\ \text{mA}$ , $f = 200\ \text{MHz}$		50		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -30\ \text{V}$ , $I_E = 0$ , $f = 1\ \text{MHz}$			9	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.





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